

Silicon PNP Power Transistors

2SB1007

DESCRIPTION

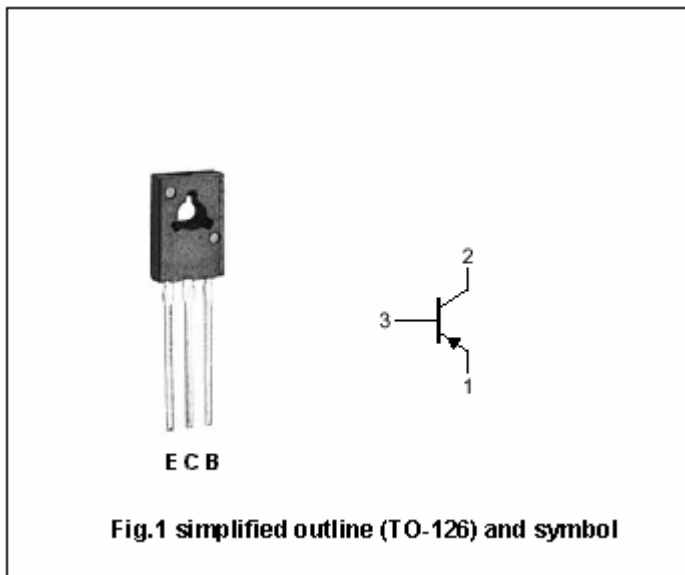
- With TO-126 package
- Complement to type 2SD1378
- High breakdown voltage

APPLICATIONS

- Low frequency power amplification

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-80	V
V _{CEO}	Collector-emitter voltage	Open base	-80	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current (DC)		-0.7	A
P _D	Total power dissipation	T _a =25	1.2	W
		T _C =25	10	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-2mA ; I _B =0	-80			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-50 μ A ; I _E =0	-80			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-50 μ A ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.5A ; I _B =-50mA		-0.2	-0.4	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V ; I _E =0			-0.5	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-4V ; I _C =0			-0.5	μ A
h _{FE}	DC current gain	I _C =-0.1A ; V _{CE} =-3V	82		390	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =-10V ; f=1MHz		14	20	pF
f _T	Transition frequency	I _E =50mA ; V _{CE} =-10V		100		MHz

◆ h_{FE} Classifications

P	Q	R
82-180	120-270	180-390

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PACKAGE OUTLINE

